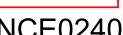
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## NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE0240 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

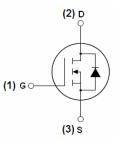
- V<sub>DS</sub> =200V,I<sub>D</sub> =40A  $R_{DS(ON)}$  <41m $\Omega$  @  $V_{GS}$ =10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



#### Schematic diagram



#### Marking and pin assignment



TO-220-3L top view

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0240	NCE0240	TO-220-3L	-	-	-

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	200	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	40	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	28	Α
Pulsed Drain Current	I <sub>DM</sub>	160	Α
Maximum Power Dissipation	P <sub>D</sub>	220	W
Derating factor		1.47	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	480	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C



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# NCE0240

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ heta JC}$	0.68	°C/W	Ì
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# Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	•					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	200	220	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =200V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2	3.2	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	36.4	41	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =25V,I <sub>D</sub> =25A	26	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -05\/\/ -0\/	-	6500	-	PF
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, F=1.0MHz	-	290	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	Γ-1.UIVIΠZ	-	220	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	26	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30V, $I_D$ =2A, $R_L$ =15 $\Omega$	-	24	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =2.5 $\Omega$	-	91	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	39	-	nS
Total Gate Charge	$Q_g$	\/ -20\/ L -20 A	-	163		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =30V, $I_{D}$ =30A, $V_{GS}$ =10V	-	31		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	64		nC
Drain-Source Diode Characteristics	•		•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =40A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	40	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 40A	-	42		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs <sup>(Note3)</sup>	-	66		nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				y LS+LD)

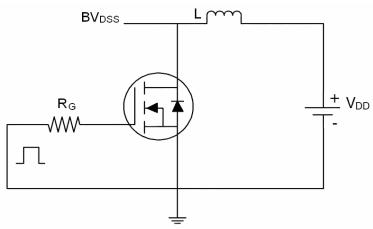
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. E\_{AS} condition: j=25  $^{\circ}\text{C}\,\text{,V}_{DD}\text{=}50\text{V},\text{V}_{G}\text{=}10\text{V},\text{L=}0.5\text{mH,Rg=}25\Omega$

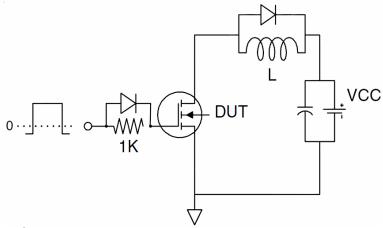
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## **Test Circuit**

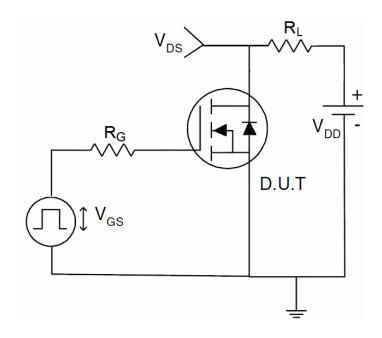
# 1) E<sub>AS</sub> test Circuits



## 2) Gate charge test Circuit

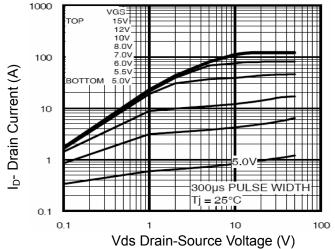


# 3) Switch Time Test Circuit

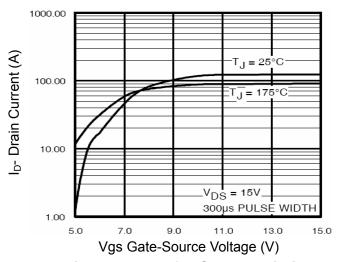


## Typical Electrical and Thermal Characteristics (Curves)

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**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

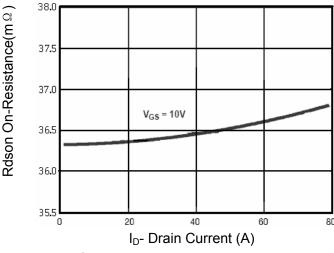


Figure 3 Rdson- Drain Current

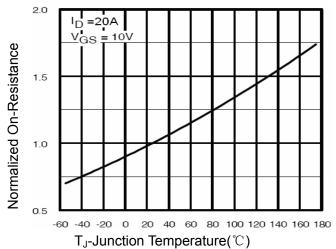


Figure 4 Rdson-JunctionTemperature

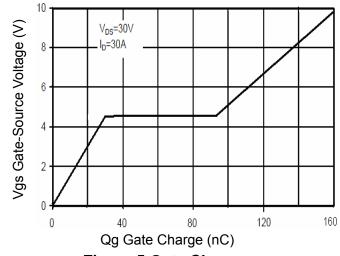
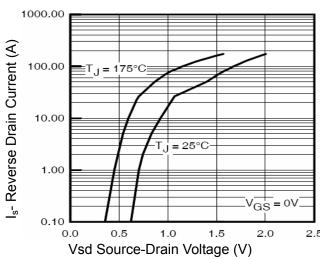


Figure 5 Gate Charge



**Figure 6 Source- Drain Diode Forward** 



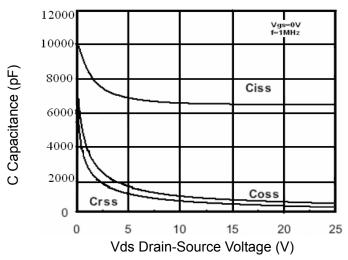


Figure 7 Capacitance vs Vds

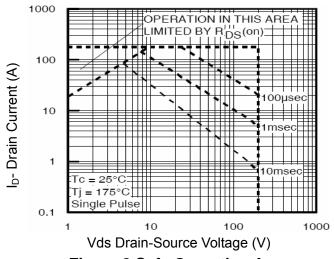


Figure 8 Safe Operation Area

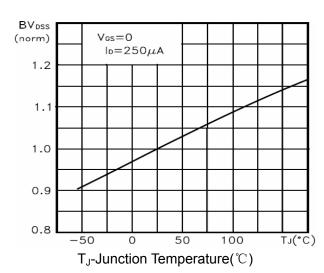


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

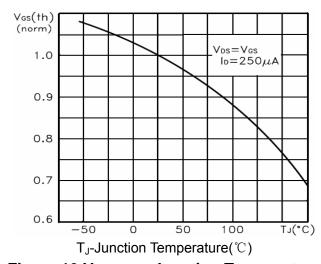


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

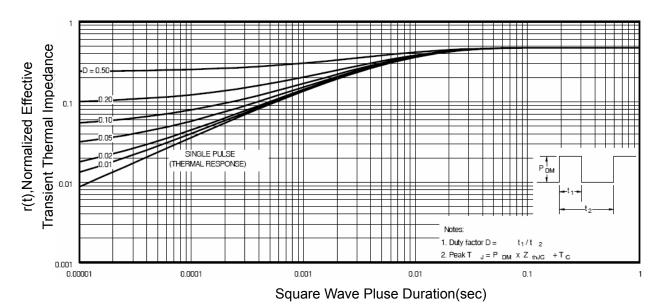
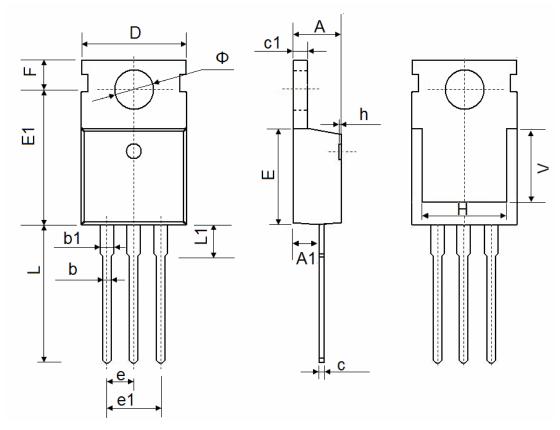


Figure 11 Normalized Maximum Transient Thermal Impedance

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# **TO-220-3L Package Information**



Comple of	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	0.100 TYP. 0.100 TYF		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500	REF.	REF. 0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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